

Features :

- Isolated mounting base 3000V~
- Pressure contact technology with Increased power cycling capability
- Space and weight saving

Typical Applications :

- Inverter
- Inductive heating
- Chopper

V _{RSM}	V _{RSM}	品名
700V	600V	Mx75DF60
900V	800V	Mx75DF80
1100V	1000V	Mx75DF100
1300V	1200V	Mx75DF120
1500V	1400V	Mx75DF140
1700V	1600V	Mx75DF160
1900V	1800V	Mx75DF180

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _j (°C)	VALUE			UNIT
				Min	Type	Max	
I _{F(AV)}	Mean forward current	180° half sine wave 50Hz Single side cooled, T _c =85°C	140			75	A
I _{F(RMS)}	RMS forward current					118	A
I _{RRM}	Repetitive peak current	at V _{RRM}	140			20	mA
I _{FSM}	Surge forward current	10ms half sine wave V _R =0.6V _{RRM}	140			2.0	kA
I ² t	I ² t for fusing coordination					20	10 ³ A ² s
V _{FO}	Threshold voltage		140			1.10	V
r _F	Forward slope resistance					3.00	mΩ
V _{FM}	Peak forward voltage	I _{FM} =225A	25			2.00	V
t _{rr}	Reverse recovery time	I _{FM} =200A, t _p =4000μs, -di/dt=20A/μs, V _R =50V	140		3.0		μs
			25		2.0		μs
R _{th(j-c)}	Thermal resistance Junction to case	D.C. Single side cooled per chip				0.310	°C/W
R _{th(c-h)}	Thermal resistance case to heatsink	D.C. Single side cooled per chip				0.080	°C/W
F _m	Terminal connection torque(M6)			4.5		6.0	N·m
	Mounting torque(M6)			4.5		6.0	N·m
V _{iso}	Isolation voltage	50Hz, R.M.S, t=1min, I _{iso} :1mA(MAX)		3000			V
T _{vj}	Junction temperature			-40		140	°C
T _{slg}	Stored temperature			-40		125	°C
W _t	Weight				320		g
Outline	M02						

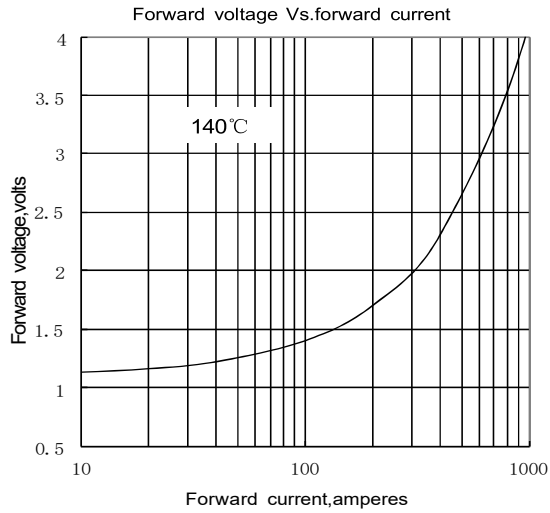


Fig.1

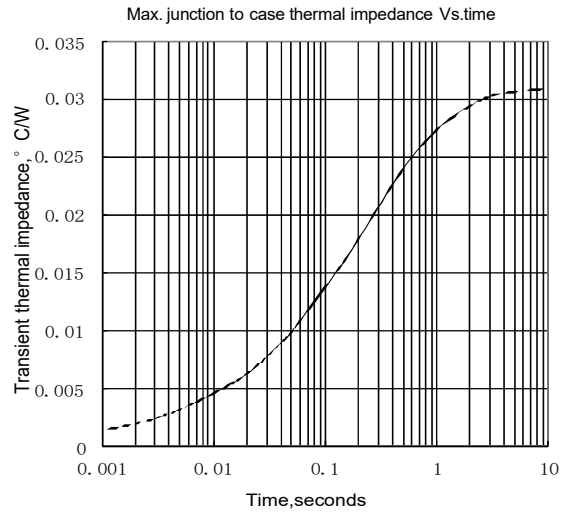


Fig.2

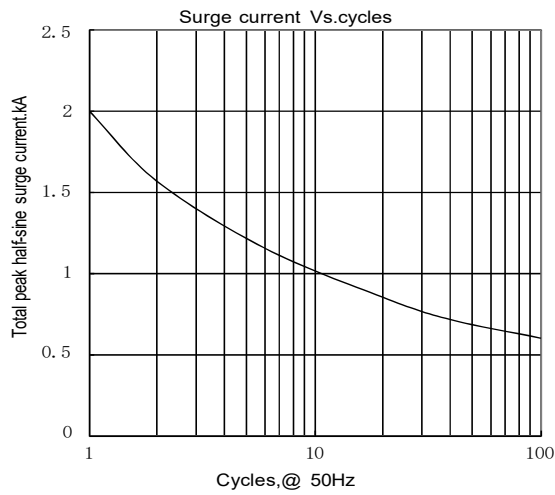
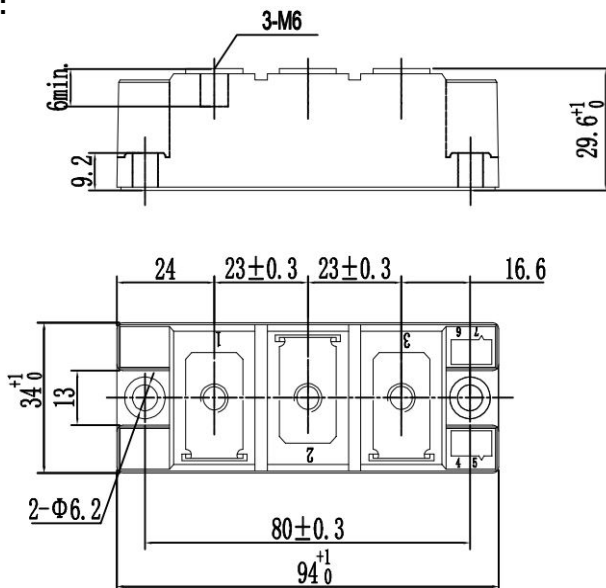


Fig.3

Outline:



Unmarked dimensional tolerance: ±0.5mm

NIPS reserves the right to change specifications without notice.

